



# UNITED STATES PATENT AND TRADEMARK OFFICE

*ccu*

UNITED STATES DEPARTMENT OF COMMERCE  
United States Patent and Trademark Office  
Address: COMMISSIONER FOR PATENTS  
P.O. Box 1450  
Alexandria, Virginia 22313-1450  
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/820,484	04/08/2004	Michael G. Kelly	10031133-1	7400
57299 7590 05/07/2007 AVAGO TECHNOLOGIES, LTD. P.O. BOX 1920 DENVER, CO 80201-1920				
			EXAMINER ANDUJAR, LEONARDO	
			ART UNIT 2826	PAPER NUMBER
			MAIL DATE 05/07/2007	DELIVERY MODE PAPER

**Please find below and/or attached an Office communication concerning this application or proceeding.**

The time period for reply, if any, is set in the attached communication.

<b>Office Action Summary</b>	Application No. 10/820,484	Applicant(s) KELLY, MICHAEL G.	
	Examiner Leonardo Andújar	Art Unit 2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

- 1) ☒ Responsive to communication(s) filed on 08 February 2007.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

- 4) ☒ Claim(s) 1-21 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-21 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
  2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

- |  |   |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892)   | 4) <input type="checkbox"/> Interview Summary (PTO-413)<br>Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)                       | 5) <input type="checkbox"/> Notice of Informal Patent Application                       |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08)<br>Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____  |

DETAILED ACTION

***Claim Rejections - 35 USC § 103***

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1-9 and 21 are rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of Wu (2003/0067057).

3. Regarding claim 1, Hideshima (e.g. fig. 8) shows an integrated circuit system, comprising: a die 11 incorporating an integrated circuit and having a top side and a bottom side, the top side supporting an electrical signal communication metallization 15 b/e wherein the bottom side supporting a bottom side thermal dissipation metallization 16/43C but does not disclose a top side thermal dissipation metallization. Nevertheless, Wu (e.g. fig. 3A) shows a die a topside thermal dissipation metallization 21. This type of embodiment allows the heat generated from a semiconductor chip to be quickly dissipated through a die pad of the lead frame after the semiconductor chip is attached to the die pad, so as to improve overall heat dissipating efficiency of the semiconductor package (pp 0009). It would have been obvious to one of ordinary skill in the art at the time the invention was made to form a top side thermal dissipation metallization layer as disclosed by Wu to allow the heat generated from a semiconductor chip to be quickly dissipated through a die pad of the lead frame after the semiconductor chip is attached

to the die pad, so as to improve overall heat dissipating efficiency of the semiconductor package as suggested by Wu.

4. Regarding claim 2, Hideshima shows that the electrical signal communication metallization comprises a plurality of exposed bonding elements on the top side of the die.

5. Regarding claim 3, Hideshima shows that the bonding elements are contained in a peripheral region of the topside of the die.

6. Regarding claim 4, Wu shows that the topside thermal dissipation metallization is disposed in a central region of the topside of the die.

7. Regarding claim 5, Wu shows that the topside thermal dissipation metallization is surrounded by the plurality of boning elements.

8. Regarding claim 6, White shows that the electrical signal communication metallization surrounds the top side thermal dissipation metallization.

9. Regarding claim 7, Hideshima shows that the topside thermal dissipation metallization comprises a patterned metal layer.

10. Regarding claim 8, Hideshima shows that the patterned metal layer comprises at least one through-hole.

11. Regarding claim 9, Hideshima shows that the patterned metal layer comprises an array of through-holes.

12. Regarding claim 21, Wu shows that the electrical signal communication metallization is free of any direct electrical connection to the top side thermal dissipation metallization on the top side of the die.

Art Unit: 2826

13. Claims 1-4 and 6-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of Kunikiyo (US 6,717,267).

14. Regarding claim 1, Hideshima shows an integrated circuit system, comprising: a die 11 incorporating an integrated circuit and having a top side and a bottom side, the top side supporting an electrical signal communication metallization 15 b/e wherein the bottom side supporting a bottom side thermal dissipation metallization 16/43C but does not disclose a top side thermal dissipation metallization. Nevertheless, Wu (e.g. fig. 3A) shows a die a topside thermal dissipation metallization 21. Nevertheless, Kunikiyo (e.g. fig. 19) shows a top side thermal dissipation metallization 31. According to Kunikiyo, this type of mounting structure provides more satisfactory effect of cooling away the heat in the interlayer insulating films than conventional semiconductor devices having no dummy interconnections or dummy plugs, since metal has higher thermal conducting rate than the interlayer insulating films. This improves the circuit operation of the semiconductor device (col. 23/lis. 1-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to include in Hideshima's invention a topside thermal dissipation metallization such as dummy patterns in accordance to Kunikiyo's invention to improve the circuit operation since the heat can be satisfactorily removed from the interlayer insulating films.

15. Regarding claim 2, Hideshima shows that the electrical signal communication metallization comprises a plurality of exposed bonding elements on the top side of the die.

16. Regarding claim 3, Hideshima shows that the bonding elements are contained in a peripheral region of the topside of the die.

17. Regarding claim 4, Kunikiyo shows that the topside thermal dissipation metallization is disposed in a central region of the topside of the die.

18. Regarding claim 6, Kunikiyo shows that the electrical signal communication metallization surrounds the topside thermal dissipation metallization (e.g. plugs).

19. Regarding claim 7, Kunikiyo shows that the topside thermal dissipation metallization comprises a patterned metal layer.

20. Regarding claim 8, Hideshima shows that the patterned metal layer comprises at least one through-hole.

21. Regarding claim 9, Hideshima shows that the patterned metal layer comprises an array of through-holes.

22. Regarding claim 10, Kunikiyo shows a top heat spreader 32 metallurgically bonded to the op side thermal dissipation metallization of the die.

23. Regarding claim 11, Kunikiyo shows that the integrated circuit is connected electrically to the op side heat spreader by an electrical path extending through the top side thermal dissipation metallization.

24. Claims 12 and 13 are rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of Kunikiyo (US 6,717,267) further in view of Wang (US 5,977,626).

25. Regarding claim 12, Hideshima in view of Kunikiyo shows most aspects of the instant invention except for an electrical interface and a substrate containing a wiring

interconnection between the electrical signal communication metallization and the electrical interface. Nevertheless, Wang (e.g. fig. 4) shows a package having a good efficiency of spreading heat and enhanced EM shielding that includes an electrical interface 28 and a substrate 20 containing a wiring interconnection between the electrical signal communication metallization and the electrical interface (col. 1/lls. 11-33; col. 2/lls. 10-14 & col. 3/lls. 10-12). It would have been obvious to one of ordinary skill in the art at the time the invention was made to use the package disclosed by Wang to package the device disclosed by Hideshima in view Kunikiyo, which includes an electrical interface and a substrate containing a wiring interconnection between the electrical signal communication metallization and the electrical interface, because this package structure has a good efficiency of spreading heat and enhanced EM shielding as taught by Wang.

26. Regarding claim 13, Wang shows a top heat spreader 32 mounted on the substrate and forms a lid of the package covering the topside of the die.

27. Claim 14 is rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of Kunikiyo (US 6,717,267) further in view of Khan et al. (US 6,853,070).

28. Regarding claim 14, Hideshima in view of Kunikiyo shows most aspects of the instant invention but does not disclose a structure having a second heat spreader or bottom heat spreader metallurgically bonded to the bottom side thermal dissipation metallization of the die. Nevertheless, Khan (e.g. fig. 2A) shows a bottom heat spreader 110 bonded to the bottom side thermal dissipation metallization of the die 102.

According to Kahn this type of mounting structure provides an improved thermal, mechanical and electrical performance because the thermal stress is reduced due to a matched thermal coefficient (col. 1/lls. 52-67; col. 2/lls. 1-6 and col. 3/lls. 14-21). It would have been obvious to one of ordinary skill in the art at the time the invention was made to metallurgically bond a bottom heat spreader to the bottom side thermal dissipation metallization of the die disclosed by Hideshima view of Kunikiyo to improve the thermal, mechanical and electrical performance of the package as taught by Khan.

29. Claims 15-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of White (US 5,665,655) further in view of Kunikiyo (US 6,717,267).

30. Regarding claim 15, Hideshima (e.g. fig. 8) shows most aspects of the instant invention including a method of making an integrated circuit system including the steps of: forming a integrated circuit dice 11 having a top supporting wherein the top supporting exposes electrical signal communication metallization 15/b/e; forming on a bottom side of the dice having a bottom side thermal dissipation metallization 16/45C; but does not include the step of forming multiple die regions on a substrate, forming a top side thermal dissipation metallization and the step of singulating the die regions to form the integrated circuit dices. Nevertheless, White (e.g. figs. 5-8) shows a method including the step of forming multiple die regions on a substrate and the step of he step of singulating the die regions to form the integrated circuit dices. This method increases the yield of devices per wafer because microcrack propagation is reduced (col. 1/lls. 50-55; col. 2/lls. 10-12 & 45-51). Kunikiyo (e.g. fig. 19) shows the step of forming a topside



thermal dissipation metallization 31. According to Kunikiyo, this type of mounting structure provides more satisfactory effect of cooling away the heat in the interlayer insulating films than conventional semiconductor devices having no dummy interconnections or dummy plugs, since metal has higher thermal conducting rate than the interlayer insulating films. This improves the circuit operation of the semiconductor device (col. 23/lis. 1-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Hideshima's method in accordance to White's teachings which include the step forming multiple die regions on a substrate and the step of the step of singulating the die regions to form the integrated circuit dices to increase the yield of devices per wafer since microcrack propagations can be reduced and to include the step of forming a topside thermal dissipation metallization such as dummy patterns in the method disclosed by Hideshima in view of White to improve the circuit operation because the heat can be satisfactorily removed form the interlayer insulating films as taught by Kunikiyo.

31. Regarding claim 16, Hideshima in view of White further in view of teaches that in each die region, the electrical signal communication metallization surrounds the topside thermal dissipation metallization.

32. Regarding claim 17, Kunikiyo teaches that each topside thermal dissipation metallization comprises an exposed metal layer with an array of through-holes (e.g. 26a).

33. Regarding claim 18, Kunikiyo (e.g. fig. 19) shows the step of metallurgically bonding a top heat spreader of the package 32 (e.g. 31) to the topside thermal dissipation metallization of the singulated die (dummy pattern 25a).

34. Claims 19 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over anticipated by Hideshima et al. (US 5,143,865) in view of White (US 5,665,655) further in view of Kunikiyo (US 6,717,267) further in view of Wang (US 5,977,626).

35. Regarding claim 19, Hideshima in view of White further in view of Kunikiyo shows most aspects of the instant invention but does not show that the package including a substrate a mounting step comprising the step of mounting the package substrate to the bottom side thermal dissipation metallization of the singulated die. Nevertheless, Wang (e.g. fig. 4) shows a method including a substrate 20 and the step of mounting the bottom side a singulated die 22 to the substrate. This package provides a good efficiency of spreading heat and enhanced EM shielding (col. 1/lls. 11-33; col. 2/lls. 10-14 & col. 3/lls. 10-12). It would have been obvious to one of ordinary skill in the art at the time the invention was made to use the method disclosed by Wang to package the device disclosed by Hideshima in view of White further in view Kunikiyo, which includes the step of mounting the bottom side a singulated die to the substrate, because this method produce a package structure having a good efficiency of spreading heat and an enhanced EM shielding as taught by Wang.

### ***Response to Arguments***

36. Applicant's arguments with respect to claims 1-21 have been considered but they are not persuasive. Applicant argues that the pad disclosed by Wu is not a metallization

since it is not a "single layer metal film or multilayer metal film formed in or on integrated circuit. Nevertheless, it is clear from figures 3a and 4 that the pad 21/31 is a single layer formed on the integrated circuit 23. As it is known in the art the leads and the die pad are separated from the frame to make the final product. Therefore, it is implicitly in the reference that the pad and the leads are independent elements and not integral component and not integral component as suggested by applicant. It is respectfully noted that a short circuit will occur if the die pad and the leads remain connected by the frame within the final package.

37. In response to applicant's argument that "Wu's disclosure, bonding pads are the only elements that are supported on the top side of the semiconductor chip 23 (see, e.g., FIG. 3A). One skilled in the art at the time the invention was made reasonably would infer from this disclosure, that the top surface of the semiconductor chip 23 is devoid of any type of structural elements designed to dissipate heat through the adhesive 212 and the die pad 21", it is respectfully noted that Wu teaches the device dissipated the heat through the adhesive/pad (pp 0032).

38. In response to applicant's arguments against the references individually, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of references. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986).

39. In response to applicant's argument that there is no suggestion to combine the references, the examiner recognizes that obviousness can only be established by

Art Unit: 2826

combining or modifying the teachings of the prior art to produce the claimed invention where there is some teaching, suggestion, or motivation to do so found either in the references themselves or in the knowledge generally available to one of ordinary skill in the art. See *In re Fine*, 837 F.2d 1071, 5 USPQ2d 1596 (Fed. Cir. 1988) and *In re Jones*, 958 F.2d 347, 21 USPQ2d 1941 (Fed. Cir. 1992). In this case, Wu (e.g. fig. 3A) shows a die a topside thermal dissipation metallization 21. This type of embodiment allows the heat generated from a semiconductor chip to be quickly dissipated through a die pad of the lead frame after the semiconductor chip is attached to the die pad, so as to improve overall heat dissipating efficiency of the semiconductor package (pp 0009).

40. Regarding applicant argument that the interconnection structure disclosed by Kunikiyo is not metallization. Nevertheless, it is clear from figure 19 that the interconnection 31 is a single layer formed on the integrated circuit. Therefore, the plugs disclosed by Kunikiyo meet applicant "definition".

41. Regarding applicant argument that the metallization 31 does not constitute a thermal dissipation it is respectfully noted that Kunikiyo explicitly teaches that the heat is dissipated through the plugs 31 (col. 9/lis. 1-6 & fig. 19).

42. In response to applicant's argument that there is no suggestion to combine Hideshima and Kunikiyo, it is noted that Kunikiyo teaches that this type of mounting structure provides more satisfactory effect of cooling away the heat in the interlayer insulating films than conventional semiconductor devices having no dummy interconnections or dummy plugs, since metal has higher thermal conducting rate than

the interlayer insulating films. This improves the circuit operation of the semiconductor device (col. 23/lis. 1-18).

### ***Conclusion***

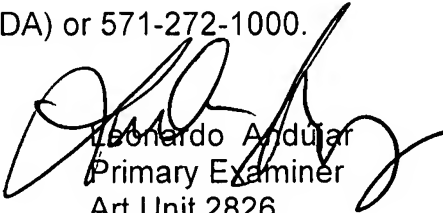
43. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Leonardo Andújar whose telephone number is 571-272-1912. The examiner can normally be reached on Mon through Thu from 9:00 AM to 7:30 PM EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue Purvis can be reached on 571-272-1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

  
Leonardo Andujar  
Primary Examiner  
Art Unit 2826

04/24/2007